

IMPROVED CONNECTION STRUCTURE FOR SOI DEVICES

ABSTRACT

[0040] A semiconductor contact connection structure and the method for forming the same are disclosed. The connection structure has a first semiconductor device formed on an insulator substrate. A non-conducting gate interconnect layer is formed on the insulator substrate for connecting to a gate of a second semiconductor device, and a silicide layer formed on the gate interconnect layer and an active region of the first semiconductor device for making a connection thereof.

Fig. 2



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